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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Application Number		09/814,023			
				Filing Date		03/20/2001			
				First Named Inventor:		Lynn Cai			
				Examiner name: J. Mancuso		GROUP: 2623			
Sheet	1	of	1	Attorney Docket Number		NTI-006			
U.S. PUBLISHED APPLICATION DOCUMENTS									
Examiner Initials*	Cited No. ¹	U.S. Patent Document Number Kind Code ² (if known)		Name of Patentee or Applicant of Cited Document		Date of Publication of Cited Document MM-DD-YYYY		Pages, Columns, Lines Where Relevant Info. Appear	
U.S. PATENT DOCUMENTS									
Examiner Initials*	Cited No. ¹	U.S. Patent Document Number Kind Code ² (if known)		Name of Patentee or Applicant of Cited Document		Date of Publication of Cited Document MM-DD-YYYY		Pages, Columns, Lines Where Relevant Info. Appear	
S.A	E1	4809341		Matsui et al.		02/28/1989			
S.A	E2	5795688		Burdorf et al.		08/18/1998			
S.A	E3	5965306		Mansfield et al.		10/12/1999			
FOREIGN PATENT DOCUMENTS									
Examiner Initials*	Cited No. ¹	Foreign Patent Document Office ³ Number ⁴ Kind Code ⁵ (if known)		Name of Patentee or Applicant of Cited Document		Date of Publication of Cited Document MM-DD-YYYY		Pages, Columns, Lines Where Relevant Info. Appear	T ⁶
S.A	F1	WO	99/14706	Ting et al.		03/25/1999			
S.A	F2	JP	2001056306	Ichiro		02/27/2001			
S.A	F3	EP	0 306 275	Yamada et al.		03/08/1989			
S.A	F4	DE	100 37 697	Aghajan		03/15/2001			
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)									
EXAMINER <i>S. J. Mancuso</i>				DATE CONSIDERED <i>3.24.04</i>					

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.

- ☒ This statement qualifies under 37 C.F.R. § 1.97, subsection (b) because (check all that apply):
- ☐ (1) It is being filed within 3 months of the application filing date and is other than a continued prosecution application under § 1.53(d)
-- OR --
 - ☐ (2) It is being filed within 3 months of entry of a national stage
-- OR --
 - ☒ (3) It is being filed before the mail date of the first Office Action on the merits.
-- OR --
 - ☐ (4) It is being filed before the mailing of a first Office Action after the filing of a request for continued examination under § 1.114
- ☐ 37 C.F.R. § 1.97(c). If this statement is being filed after the period specified in § 1.97(b), but before the mailing date of the earlier of a final office action under § 1.113, a notice of allowance under § 1.311, or an action that otherwise closes prosecution in the application, then:
- ☐ a certification as specified in § 1.97(e) is provided below; **or**
 - ☐ a fee of \$180.00 as set forth in § 1.17(p) is authorized below, enclosed, or included with the payment of other papers filed together with this statement.
- ☐ 37 C.F.R. § 1.97(d). If this statement is being filed after the period specified in § 1.97(c), but on or before payment of the issue fee, then:
- A. a certification as specified in § 1.97(e) is completed below; **and**
 - B. a fee of \$180.00 as set forth in § 1.17(p) is authorized below, enclosed, or included with the payment of other papers filed together with this statement.
- ☒ **Fee Authorization.** The Commissioner is hereby authorized to charge any additional fees or credit any overpayment associated with this communication to Deposit Account No. 50-0574 (Docket No. NTI-006).


Respectfully submitted,

BEVER, HOFFMAN & HARMS, LLP

Dated: 2-7-03

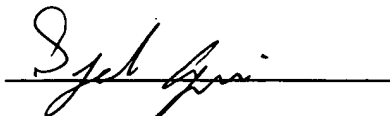
By: 
Jeanette S. Harms, Reg. No. 35,537

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INFORMATION DISCLOSURE CITATION 		Atty. Docket No. NTI-006	Serial No. 09/814,023			
		Applicant CAI, Lynn	Group 2623			
		Filing Date 3/20/2001				
U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
S.A	6,130,750	10/10/2000	Ausschnitt, et al.	356	401	8/28/1997
S.A	6,346,426 B1	2/12/2002	Toprac, et al.	438	8	11/17/2000

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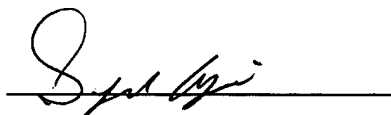
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INFORMATION DISCLOSURE CITATION PTO-1449		Atty. Docket No. NTI-006		Serial No. 09/814,023		
		Applicant CAI, Lynn		Group 2623		
		Filing Date 3/20/2001				
U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
S.A	2002/0164064 A1	11/7/2002	Karklin, et al.	382	145	3/20/2001
S.A	2002/0164065 A1	11/7/2002	Cai, et al.	382	149	3/20/2001

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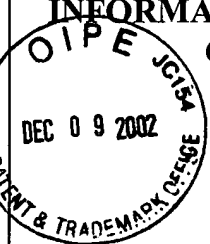
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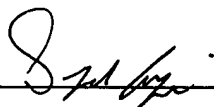
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<p align="center">INFORMATION DISCLOSURE CITATION</p> <p align="center">PTO-1449</p> 	<p>Atty. Docket No. NTI-006</p> <p>Applicant CAI, Lynn</p> <p>Filing Date 3/20/2001</p>	<p>Serial No. 09/814,023</p> <p>Group 2623</p>
	<p align="center">OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</p>	
<p>EXAMINER'S INITIALS</p>	<p>CITATION</p>	
<p>S.A</p>	<p>Lin, B.J., et al., "Single-Level Electric Testsites for Phase-Shifting Masks", SPIE, Vol. 1673, pp. 221-228, March 9-11, 1992.</p>	

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INFORMATION DISCLOSURE CITATION PTO-1449	Atty. Docket No. NTI-006	Serial No. 09/814,023
	Applicant CAI, Lynn	RECEIVED AUG 13 2002
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U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
S.A	6,016,357	1/18/2000	Neary, et al.	382	144	6/16/1997
	6,023,328	2/8/2000	Pierrat	356	237.4	2/23/1998
	6,076,465	6/20/2000	Vacca, et al.	101	481	9/19/1997
	6,091,845	7/18/2000	Pierrat, et al.	382	144	2/24/1998
	6,272,236	8/7/2001	Pierrat, et al.	382	144	7/18/2000
	6,334,209 B1	12/25/2001	Hashimoto, et al.	716	21	9/2/1999
	2002/0019729 A1	2/14/2002	Chang, et al.	703	6	8/7/1998

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CITATION

PTO-1449

Atty. Docket No.

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Serial No.

09/814,023

Applicant

CAI, Lynn

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FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
S.A	WO 97/13370	4/10/1997	WO			<input type="checkbox"/>	<input type="checkbox"/>
	WO 98/20327	5/14/1998	WO			<input type="checkbox"/>	<input type="checkbox"/>
	WO 98/45685	10/15/1998	WO			<input type="checkbox"/>	<input type="checkbox"/>
	WO 99/38002	7/29/1999	WO			<input type="checkbox"/>	<input type="checkbox"/>
	WO 99/56113	11/4/1999	WO			<input type="checkbox"/>	<input type="checkbox"/>
	WO 99/59200	11/18/1999	WO			<input type="checkbox"/>	<input type="checkbox"/>
	WO 99/67626	12/29/1999	WO			<input type="checkbox"/>	<input type="checkbox"/>
	WO 99/14706 A2/A3	3/25/1999	WO			<input type="checkbox"/>	<input type="checkbox"/>

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	Applicant CAI, Lynn	RECEIVED AUG 13 2002
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITATION
S.A	Spence, C., et al., "Detection of 60(degree) Phase Defects on Alternating PSMs", Advanced Micro Devices, KLA-Tencor, DuPont RTC (2 pages).
	Ogawa, K., et al., "Phase Defect Inspection by Differential Interference", Lasertec Corporation (12 pages).
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	Hemar, S., et al., "Finding Killer CD Variations by Full-Reticle CD Mapping", Microlithography World, pp. 4, 6, 8 & 10 (Summer 2000).

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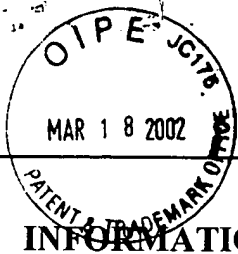
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	NTI-006	09/814,023
	Applicant	
	CAI, Lynn	
	Filing Date	Group
	3/20/2001	3742

U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
S.A	6,081,659	6/27/2000	Garza, et al.	395	500.22	4/26/1999
S.A	6,171,731 B1	1/9/2001	Medvedeva, et al.	430	5	1/20/1999

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	Applicant CAI, Lynn	
	Filing Date 3/20/2001	Group 3742

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITATION
D.A.	Adam, K., et al., "Simplified Models for Edge Transitions in Rigorous Mask Modeling", University of California Berkeley (40 pages).
	Gordon, R., et al., "Mask Topography Simulation for EUV Lithography", FINLE Technologies Inc. (15 pages).
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	Balasinski, A., et al., "A Novel Approach to Simulate the Effect of Optical Proximity on MOSFET Parametric Yield", IEEE, pp. 37.6.1-37.6.4 (1999).
↓	Balasinski, A., et al., "Comparison of Mask Writing Tools and Mask Simulations for 0.16um Devices", IEEE, SEMI Advanced Semiconductor Manufacturing Conference, pp. 372-377 (1999).

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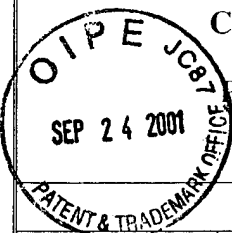
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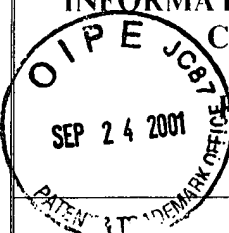
INFORMATION DISCLOSURE CITATION  PTO-1449		ATTY. DOCKET NO. NTI-006		SERIAL NO. 09/814,023		
		APPLICANT Cai, et al.				
		FILING DATE 3/20/01		GROUP 3742		
U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
S.A.	5,326,659	7/5/94	Liu, et al.	430	5	3/5/92
	5,340,700	8/23/94	Chen, et al.	430	312	11/3/93
	5,432,714	7/11/95	Chung, et al.	364	525	9/2/94
	5,572,598	11/5/96	Wihl, et al.	382	144	2/25/94
	5,795,688	8/18/98	Burdorf, et al.	430	30	8/14/96
	5,801,954	9/1/98	Le, et al.	364	488	4/24/96
	5,804,340	9/8/98	Garza, et al.	430	5	12/23/96
	5,815,685	9/29/98	Kamon	395	500	9/15/95
	5,825,647	10/20/98	Tsudaka	364	167.03	3/12/96
	5,849,440	12/15/98	Lucas, et al.	430	5	1/29/97
	5,862,058	1/19/99	Samuels, et al.	364	491	5/16/96
	5,900,338	5/4/99	Garza, et al.	430	5	8/15/97
	6,009,250	12/28/99	Ho, et al.	395	500.06	9/30/97
	6,009,251	12/28/99	Ho, et al.	395	500.06	9/30/97
6,011,911	1/4/00	Ho, et al.	395	500.06	9/30/97	
6,078,738	6/20/00	Garza, et al.	395	500.22	5/8/97	
EXAMINER <i>S.A.</i>			DATE CONSIDERED <i>3.24.04</i>			

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FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
S.A	WO 00/36525 A3	6/22/00	PCT			<input type="checkbox"/>	<input type="checkbox"/>
S.A	WO 00/67074 A1	11/9/00	PCT			<input type="checkbox"/>	<input type="checkbox"/>
S.A	WO 00/67075 A1	11/9/00	PCT			<input type="checkbox"/>	<input type="checkbox"/>
	WO 00/67076 A1	11/9/00	PCT			<input type="checkbox"/>	<input type="checkbox"/>
						<input type="checkbox"/>	<input type="checkbox"/>
						<input type="checkbox"/>	<input type="checkbox"/>
						<input type="checkbox"/>	<input type="checkbox"/>
						<input type="checkbox"/>	<input type="checkbox"/>
						<input type="checkbox"/>	<input type="checkbox"/>
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
S.A		Brunner, T. et al., "Approximate Models For Resist Processing Effects", <i>SPIE</i> , Vol. 2726, pp. 198-207, March 1996.	
		Casey, Jr., J.D. et al., "Chemically Enhanced FIB Repair Of Opaque Defects On Molybdenum Silicide Photomasks", <i>SPIE</i> , Vol. 3236, pp. 487-497 (1997).	
		Chang, K. et al., "Accurate Modeling of Deep Submicron Interconnect Technology", <i>TMA Times</i> , Vol. IX, No. 3 (1997).	
		Cobb, et al., "Fast Sparse Aerial Image Calculation For OPC", <i>SPIE</i> , Vol. 2621, pp. 534-544	
		Fukuda, H. et al., "Determination Of High-Order Lens Aberration Using Phase/Amplitude Linear Algebra", <i>J. Vac. Sci. Technol. B</i> , Vol. 17, No. 6, pp. 3318-3321, November/December 1999.	
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		Ham, Y.M. et al., "Dependence Of Defects In Optical Lithography", <i>Jpn. J. Appl. Phys.</i> , Vol. 31, pp. 4137-4142 (1992).	
		Henke, W. et al., "A Study Of Reticle Defects Imaged Into Three-Dimensional Developed Profiles Of Positive Photoresist Using The Solid Lithography Simulator", <i>Microelectronics Eng.</i> , Vol. 14, pp. 283-297 (1991).	
		Ibsen, K. et al., "Clear Field Reticle Defect Disposition For Advanced Sub-Half Micron Lithography", <i>SPIE</i> , Proceedings of the 17 th Annual Symposium on Photomask Technology and Management, Vol. 3236, pp. 124-135 (1997).	
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		Kubota, H. et al., "A Fast Method Of Simulating Resist Pattern Contours Based On Mean Inhibitor Concentration", <i>Jpn. J. Appl. Phys.</i> , Vol. 37, pp. 5815-5820 (1998).	
		Neureuther, A., "Modeling Phase Shifting Masks", <i>SPIE</i> , 10 th Annual Symposium on Microlithography, Vol. 1496, pp. 80-85 (1990).	
EXAMINER	S. A. [Signature]	DATE CONSIDERED	3.24.04

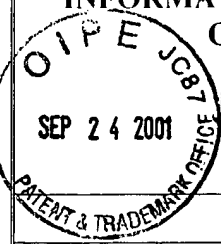

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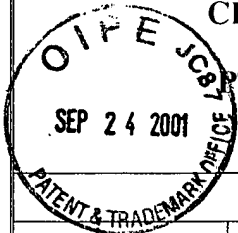
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
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